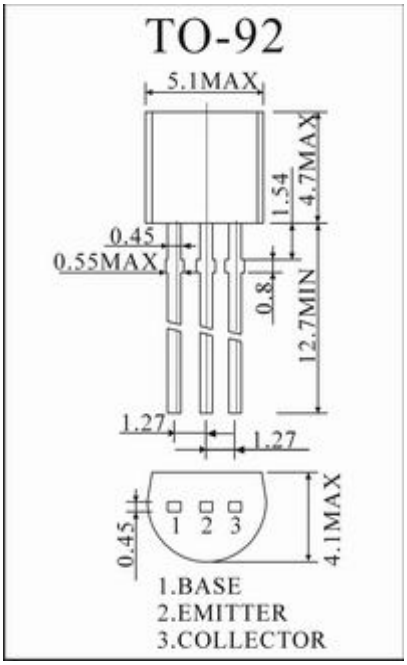
Guangdong Yuejing High Technology CO.,LTD.

C3779

—NPN silicon —

■■**APPLICATION:** **POWER AMPLIFIER APPLICATION、**

SWITCHING APPLICATION.



■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	100	mA
Collector Power Dissipation	P_C	600	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃

■■ **ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	40		200		V_{CE}=10 V，Ic=20 mA
Collector Cut-off Current	I_{CBO}			1	μA	V_{CB}=12 V，I_E=0
Emitter Cut-off Current	I_{EBO}			10	μA	V_{EB}=2 V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	20			V	Ic=0.1 mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	12			V	Ic= 1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	3			V	I_E= 0.1mA，Ic=0
Gain bandwidth product	f_T	2	5		GHz	Ic=20 mA，V_{CE}=10 V
Common Base Output Capacitance	Cob		1		PF	V_{CB}= 10V，I_E=0，f = 1 MHz
Noise Figure	N_F		1.5	3	dB	V_{CE}=10 V,I_C= 5mA,f=0.9GMHz

■■h_{FE} **Classification And Marking**

Classification	C	D	E
h_{FE}	40～80	60～120	100～200